

Effect of multilayer structure, stacking order and external electric field on electrical properties of few-layer boron-phosphide

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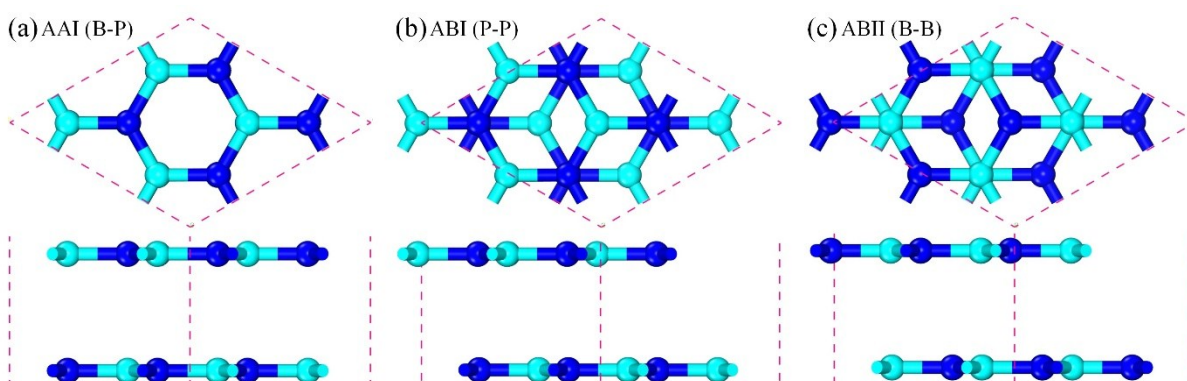
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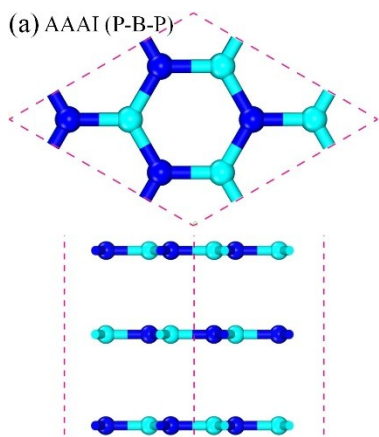
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Bilayer stacking pattern

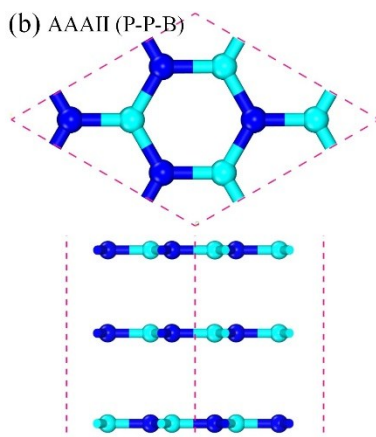


Trilayer stacking pattern

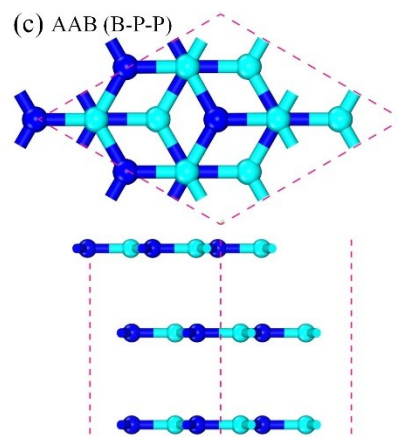
(a) AAI (P-B-P)



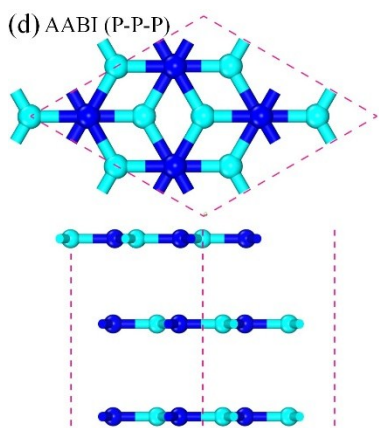
(b) AAII (P-P-B)



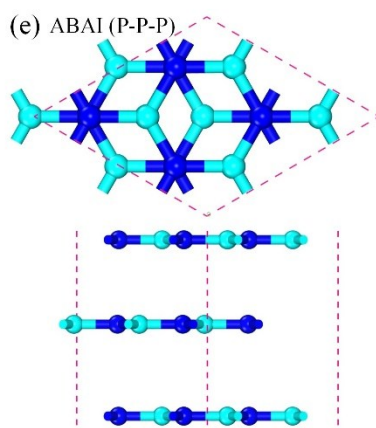
(c) AAB (B-P-P)



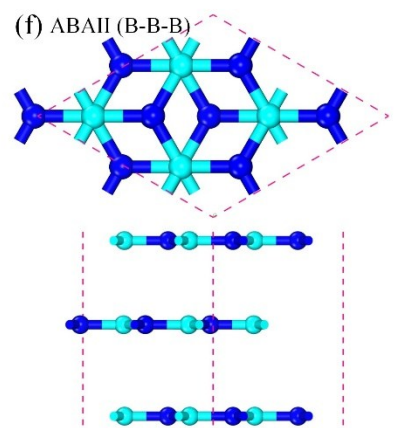
(d) AABI (P-P-P)



(e) ABAI (P-P-P)



(f) ABII (B-B-B)



(g) ABIII (B-P-B)

